

## Study of Ion Beam Mixing of Te/In and Se/In systems by Cascade Collisional Mixing Model

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Ion Beam Mixing at room temperature of Te/In and Se/In bilayer systems induced by 400 KeV Ar<sup>+</sup> ions from Jordan Van De Graaff Accelerator with fluences ranging from  $1.11 \times 10^{14}$  -  $7 \times 10^{15}$  ions/cm<sup>2</sup> for Te/In system and  $1.35 \times 10^{14}$  -  $2.3 \times 10^{16}$  ions/cm<sup>2</sup> for Se/In system. The systems are studied by means of AC electrical resistivity measurement, which shows higher mixing efficiency of Se/In system than Te/In system, and by 2 MeV He<sup>+</sup> backscattering spectrometry, which shows the width of intermixed layers are 100 nm and 50 nm for Se/In and Te/In respectively.

Ion Beam Mixing for these systems are studied theoretically by cascade collisional mixing "Haff and Switkowski" model, the nuclear stopping powers are calculated by TRIM computer code. The diffusion rate is calculated for the systems Te/In and Se/In, which showed that the diffusion rate and mixed layer for the system Se/In is greater than that of Te/In, which agree with experimental results. The theoretical study is a tool and indication to determine the efficiency of mixing between upper and lower layers before preparation and irradiation of samples, which provide the effort and money.

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